

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ferroelectric film that is described by a general formula  $\text{AB}_{1-x}\text{Nb}_x\text{O}_3(\text{Pb}_y\text{A})_y(\text{B}_{1-x}\text{Nb}_x)\text{O}_3$ ,

wherein an A element ~~includes~~ comprises at least ~~Pb~~ one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu,

wherein a B element ~~includes~~ comprises at least one of Zr, Ti, V, W, Hf and Ta, and

wherein ~~Nb<sub>x</sub>~~ is ~~included~~ within the range of:  $0.05 \leq x \leq 0.4$ .

2. (Currently Amended) ~~The A ferroelectric film as defined by claim 1 that is described by~~  $(\text{Pb}_{1-y}\text{A}_y)(\text{B}_{1-x}\text{Nb}_x)\text{O}_3$ ,

wherein ~~the an~~ A element ~~includes~~ Pb<sub>1-y</sub>Ln<sub>y</sub> comprises at least one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu, and

wherein ~~Ln~~ includes at least one of La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu, and y is within the range of:  $0 < y \leq 0.2$ ,

wherein a B element comprises at least one of Zr, Ti, V, W, Hf and Ta, and

wherein x is within the range of:  $0.05 \leq x \leq 0.4$ .

3-7. (Canceled)

8. (Currently Amended) ~~The PZT family~~ ferroelectric film as defined by claim ~~51~~, comprising:

Si, ~~Ge~~ or Si and Ge ~~of at least 0.5 mol%~~.

9. (Currently Amended) ~~The PZT family~~ ferroelectric film as defined by claim ~~51~~, comprising:

Si, Ge or Si and Ge of at least from about 0.5 mol% and less than to about 5  
mol%.

10-23. (Canceled)

24. (Currently Amended) A ferroelectric memory ~~manufactured by using the~~  
~~manufacture method as defined by any one of claims 1 to 13~~ device comprising:

a substrate;

a transistor formed on the substrate; and

a ferroelectric capacitor formed above the substrate,

wherein the ferroelectric capacitor comprises a ferroelectric film as defined by  
claim 1.

25. (Currently Amended) A piezoelectric ~~element~~ actuator comprising the  
~~ferroelectric film as defined by any one of claims 1 to 13 or the ferroelectric capacitor as~~  
~~defined by claim 23:~~

a substrate; and

a piezoelectric element formed above the substrate,

wherein the piezoelectric element comprises a ferroelectric film as defined by  
claim 1.

26. (Canceled)

27. (New) The ferroelectric film as defined by claim 2, comprising:

Si, Ge or Si and Ge.

28. (New) The ferroelectric film as defined by claim 2, comprising:

Si, Ge or Si and Ge of from about 0.5 mol% to about 5 mol%.

29. (New) A ferroelectric memory device comprising:

a substrate;

a transistor formed on the substrate; and

a ferroelectric capacitor formed above the substrate,  
wherein the ferroelectric capacitor comprises a ferroelectric film as defined by  
claim 2.

30. (New) A piezoelectric actuator comprising:  
a substrate; and  
a piezoelectric element formed above the substrate,  
wherein the piezoelectric element comprises a ferroelectric film as defined by  
claim 2.